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www.vishay.com

SIHA15N50E

Vishay Siliconix

E Series Power MOSFET

PRODUCT SUMMARY	
V_{DS} (V) at T_J max.	550
$R_{DS(on)}$ max. at 25 °C (Ω)	$V_{GS} = 10\text{ V}$ 0.243
Q_g max. (nC)	66
Q_{gs} (nC)	8
Q_{gd} (nC)	14
Configuration	Single

FEATURES

- Low figure-of-merit (FOM) $R_{on} \times Q_g$
- Low input capacitance (C_{iss})
- Reduced switching and conduction losses
- Low gate charge (Q_g)
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

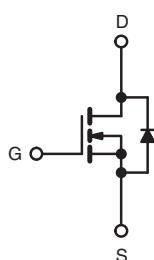
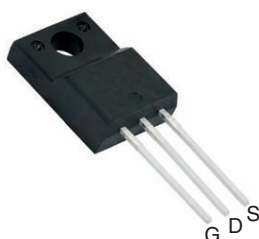


RoHS
COMPLIANT

APPLICATIONS

- Computing
 - PC silver box / ATX power supplies
- Lighting
 - Two stage LED lighting
- Consumer electronics
- Applications using hard switched topologies
 - Power factor correction (PFC)
 - Two switch forward converter
 - Flyback converter
- Switch mode power supplies (SMPS)

Thin-Lead TO-220 FULLPAK



N-Channel MOSFET

ORDERING INFORMATION	
Package	Thin-Lead TO-220 FULLPAK
Lead (Pb)-free	SIHA15N50E-E3


ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ °C}$, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	500	V
Gate-Source Voltage	V_{GS}	± 30	
Continuous Drain Current ($T_J = 150\text{ °C}$) ^e	V_{GS} at 10 V	$T_C = 25\text{ °C}$	14.5
		$T_C = 100\text{ °C}$	9.2
Pulsed Drain Current ^a	I_{DM}	28	A
Linear Derating Factor		1.25	W/°C
Single Pulse Avalanche Energy ^b	E_{AS}	136	mJ
Maximum Power Dissipation	P_D	33	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	°C
Drain-Source Voltage Slope	$V_{DS} = 0\text{ V to } 80\% V_{DS}$	70	V/ns
Reverse Diode dV/dt ^d		27	
Soldering Recommendations (Peak Temperature) ^c	for 10 s	300	°C

Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50\text{ V}$, starting $T_J = 25\text{ °C}$, $L = 28.2\text{ mH}$, $R_g = 25\text{ }\Omega$, $I_{AS} = 3.1\text{ A}$.
- 1.6 mm from case.
- $I_{SD} \leq I_D$, $dI/dt = 100\text{ A}/\mu\text{s}$, starting $T_J = 25\text{ °C}$.
- Limited by maximum junction temperature.

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	65	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	3.8	



SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	500	-	-	V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	Reference to 25 °C, I _D = 1 mA	-	0.62	-	V/°C
Gate-Source Threshold Voltage (N)	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2.0	-	4.0	V
Gate-Source Leakage	I _{GSS}	V _{GS} = ± 20 V	-	-	± 100	nA
		V _{GS} = ± 30 V	-	-	± 1	μA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 500 V, V _{GS} = 0 V	-	-	10	μA
		V _{DS} = 400 V, V _{GS} = 0 V, T _J = 125 °C	-	-	25	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 10 V I _D = 7.5 A	-	0.243	0.280	Ω
Forward Transconductance	g _{fs}	V _{DS} = 30 V, I _D = 7.5 A	-	3.9	-	S
Dynamic						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 100 V, f = 1 MHz	-	1162	-	pF
Output Capacitance	C _{oss}		-	51	-	
Reverse Transfer Capacitance	C _{rss}		-	7	-	
Effective Output Capacitance, Energy Related ^a	C _{o(er)}	V _{DS} = 0 V to 400 V, V _{GS} = 0 V	-	55	-	pF
Effective Output Capacitance, Time Related ^b	C _{o(tr)}		-	164	-	
Total Gate Charge	Q _g	V _{GS} = 10 V I _D = 7.5 A, V _{DS} = 400 V	-	33	66	nC
Gate-Source Charge	Q _{gs}		-	8	-	
Gate-Drain Charge	Q _{gd}		-	14	-	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 400 V, I _D = 12 A, V _{GS} = 10 V, R _g = 9.1 Ω	-	15	30	ns
Rise Time	t _r		-	24	48	
Turn-Off Delay Time	t _{d(off)}		-	34	68	
Fall Time	t _f		-	18	36	
Gate Input Resistance	R _g	f = 1 MHz, open drain	-	0.85	-	Ω
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	14.5	A
Pulsed Diode Forward Current	I _{SM}		-	-	28	
Diode Forward Voltage	V _{SD}	T _J = 25 °C, I _S = 7.5 A, V _{GS} = 0 V	-	-	1.2	V
Reverse Recovery Time	t _{rr}	T _J = 25 °C, I _F = I _S = 7.5 A, dI/dt = 100 A/μs, V _R = 25 V	-	265	-	ns
Reverse Recovery Charge	Q _{rr}		-	3.2	-	μC
Reverse Recovery Current	I _{RRM}		-	23	-	A

Notes

- a. C_{oss(er)} is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}.
 b. C_{oss(tr)} is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}.



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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

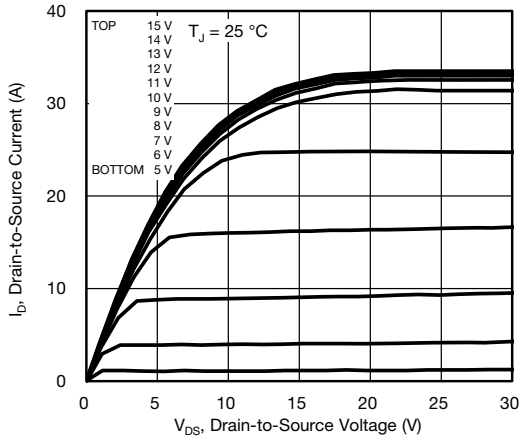


Fig. 1 - Typical Output Characteristics

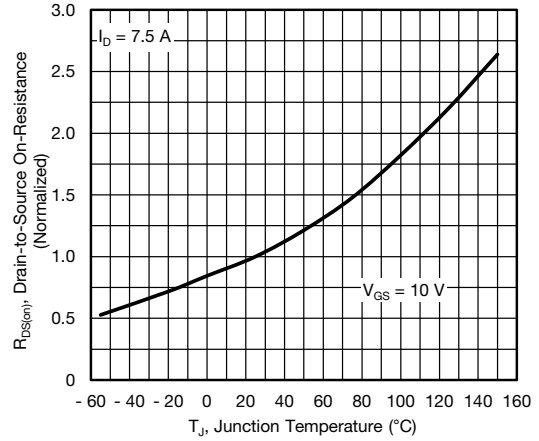


Fig. 4 - Normalized On-Resistance vs. Temperature

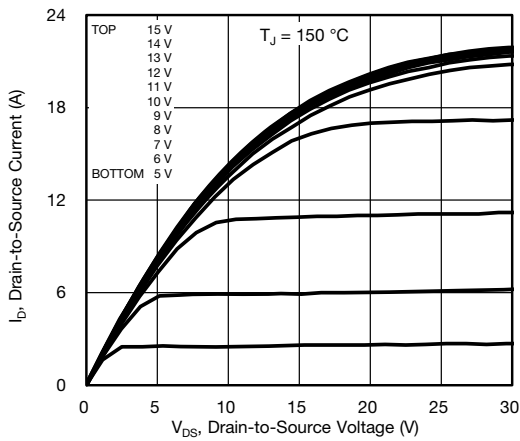


Fig. 2 - Typical Output Characteristics

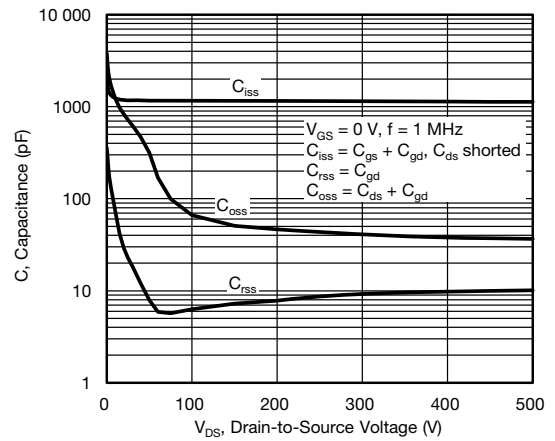


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

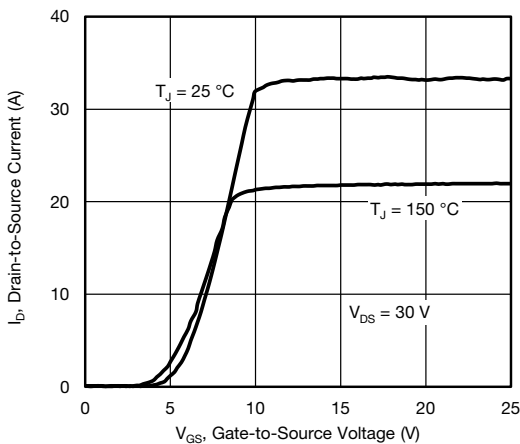


Fig. 3 - Typical Transfer Characteristics

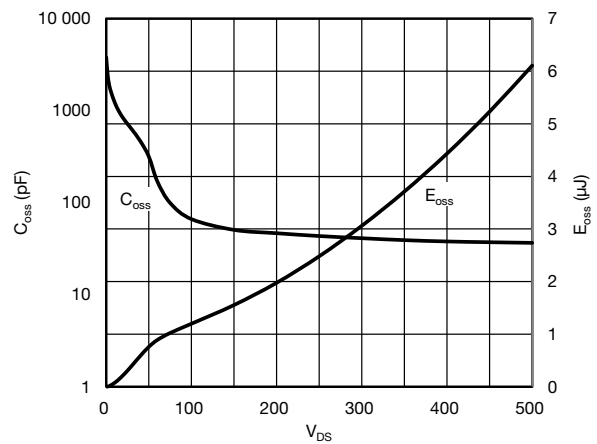


Fig. 6 - C_{oss} and E_{oss} vs. V_{DS}

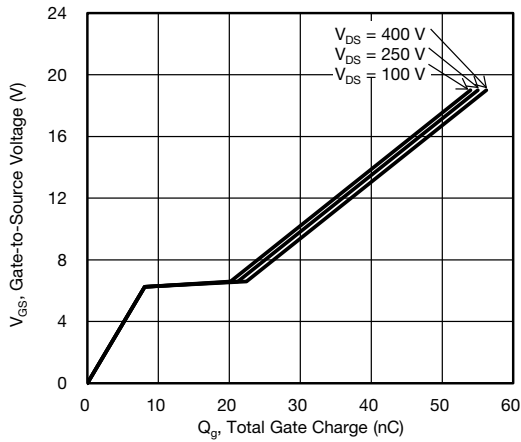


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

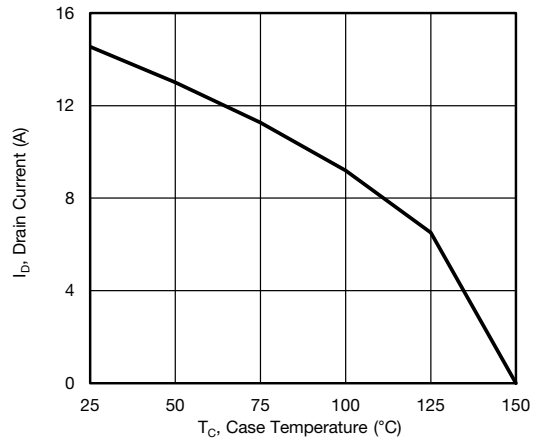


Fig. 10 - Maximum Drain Current vs. Case Temperature

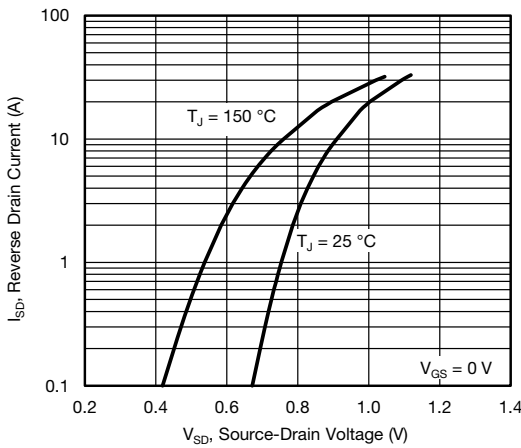


Fig. 8 - Typical Source-Drain Diode Forward Voltage

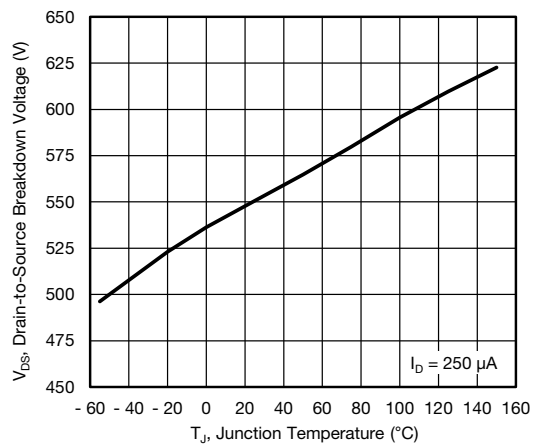


Fig. 11 - Temperature vs. Drain-to-Source Voltage

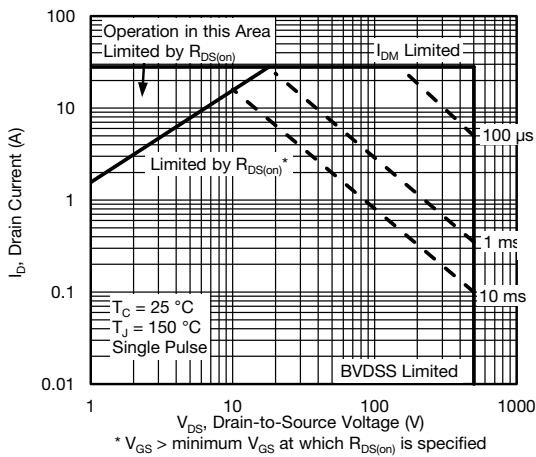


Fig. 9 - Maximum Safe Operating Area

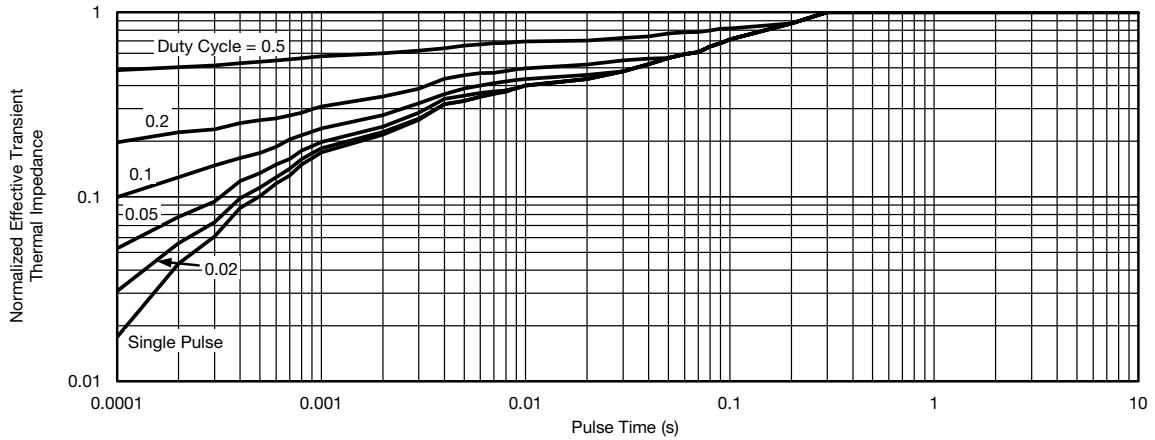


Fig. 12 - Normalized Thermal Transient Impedance, Junction-to-Case

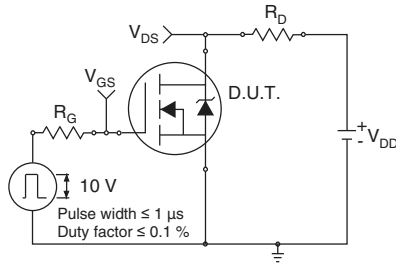


Fig. 13 - Switching Time Test Circuit

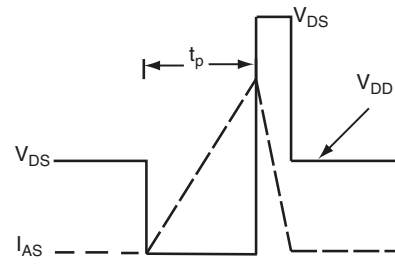


Fig. 16 - Unclamped Inductive Waveforms

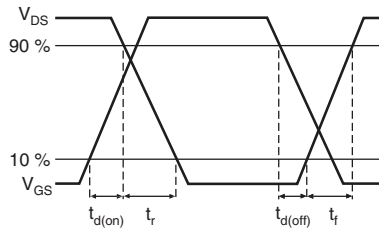


Fig. 14 - Switching Time Waveforms

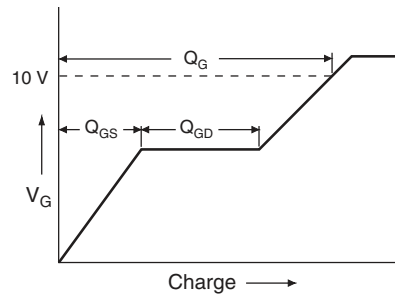


Fig. 17 - Basic Gate Charge Waveform

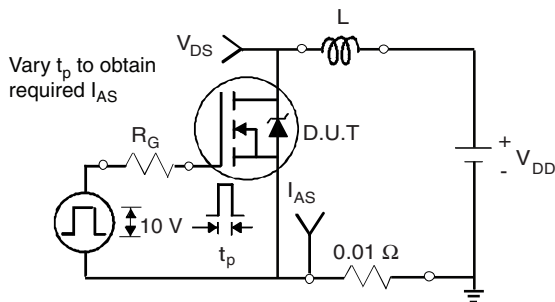


Fig. 15 - Unclamped Inductive Test Circuit

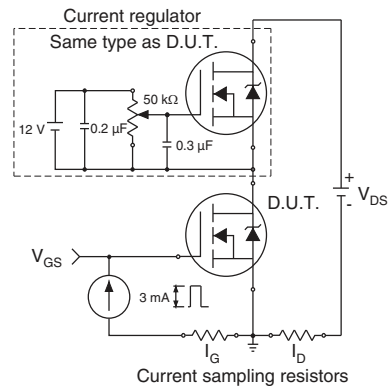
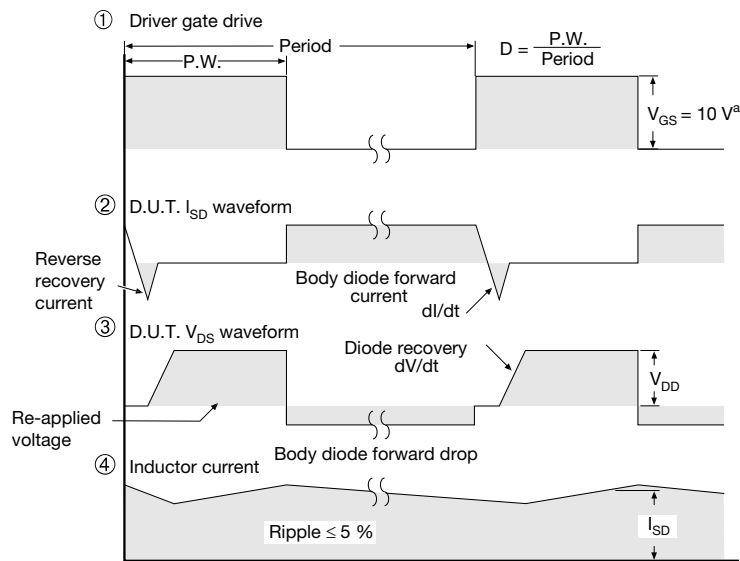
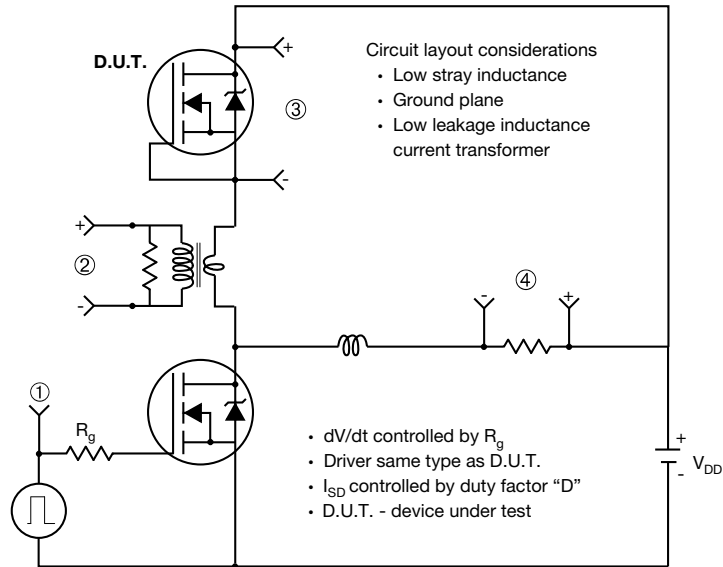


Fig. 18 - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



Note

a. $V_{GS} = 5 V$ for logic level devices

Fig. 19 - For N-Channel

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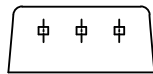
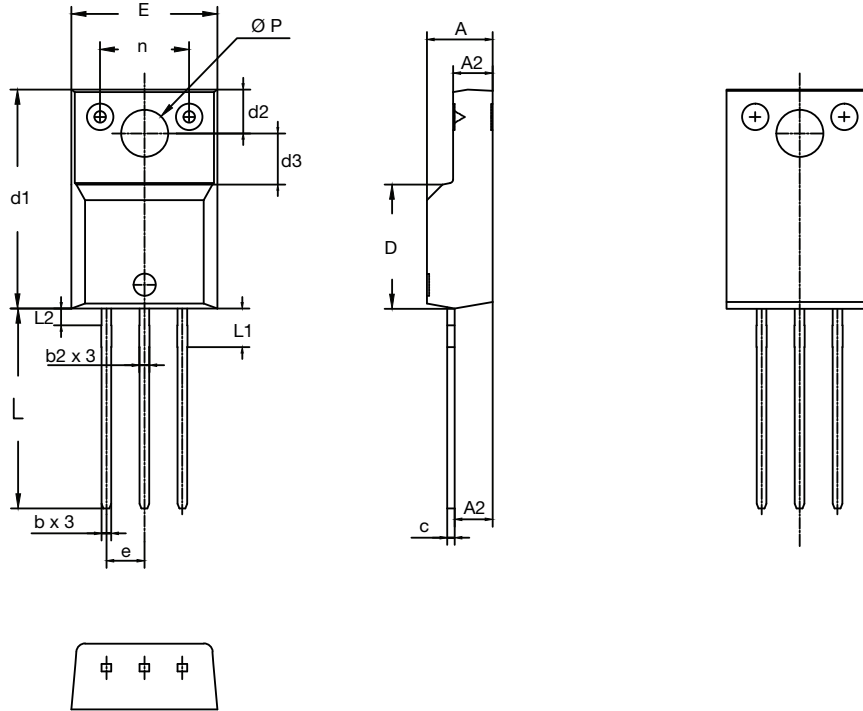


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Package Information

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TO-220 FULLPAK Thin Lead



SYMBOL	DIMENSIONS			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.30	4.70	0.169	0.185
A1	2.50	2.90	0.098	0.114
A2	2.50	2.70	0.098	0.106
b	0.60	0.80	0.024	0.031
b2	0.60	0.90	0.024	0.035
c	-	0.60	-	0.024
D	8.30	8.70	0.327	0.342
d1	14.70	15.30	0.579	0.602
d2	2.90	3.10	0.114	0.122
d3	3.40	3.60	0.134	0.142
E	9.70	10.30	0.382	0.406
e	2.50	2.70	0.098	0.106
L	13.40	13.80	0.528	0.543
L1	2.50	2.80	0.098	0.110
L2	-	1.20	-	0.047
n	6.05	6.15	0.238	0.242
Ø P	3.00	3.40	0.118	0.134

ECN: X15-0319-Rev. B, 12-Oct-15
 DWG: 6021



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